P-Channel 60-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[d]
–60	0.0069 @ V_{GS} = –10 V	–110
	0.0088 @ V_{GS} = –4.5 V	–110

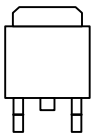
FEATURES

- TrenchFET® Power MOSFET
- New Package with Low Thermal Resistance

APPLICATIONS

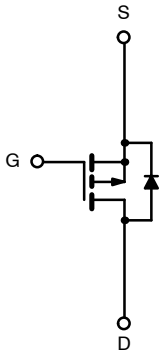
- Automotive
  - 12-V Boardnet
  - High-Side Switches
  - Motor Drives

TO-263



Top View

Ordering Information: SUM110P06-07L
SUM110P06-07L—E3 (Lead Free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	–60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[d] (T_J = 175°C)	T_C = 25°C	I_D	–110	A
	T_C = 125°C		–95	
Pulsed Drain Current		I_{DM}	–240	
Avalanche Current	L = 0.1 mH	I_{AS}	–75	
Single Pulse Avalanche Energy[a]		E_{AS}	281	mJ
Power Dissipation	T_C = 25°C	P_D	375[c]	W
	T_A = 25°C[b]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient PCB Mount[b]	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	0.4	

Notes:
a. Duty cycle ≤ 1%.
b. When mounted on 1" square PCB (FR-4 material).
c. See SOA curve for voltage derating.
d. Limited by package.

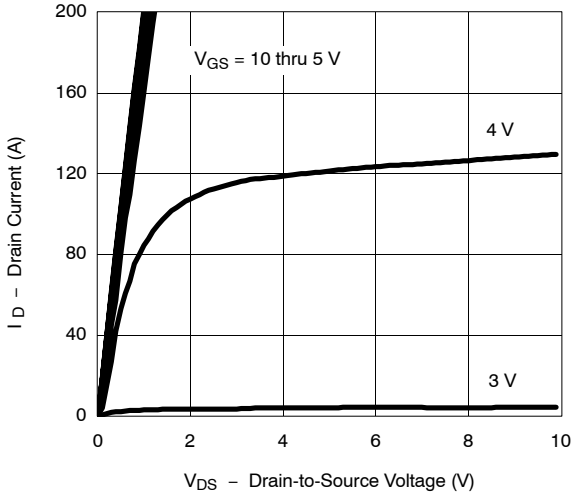
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA	−60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = −250 μA	−1		−3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = −60 V, V_{GS} = 0 V			−1	μA
		V_{DS} = −60 V, V_{GS} = 0 V, T_J = 125°C			−50	
		V_{DS} = −60 V, V_{GS} = 0 V, T_J = 175°C			−250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = −5 V, V_{GS} = −10 V	−120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = −10 V, I_D = −30 A		0.0055	0.0069	Ω
		V_{GS} = −10 V, I_D = −30 A, T_J = 125°C			0.0115	
		V_{GS} = −10 V, I_D = −30 A, T_J = 175°C			0.0138	
		V_{GS} = −4.5 V, I_D = −20 A		0.007	0.0088	
Forward Transconductance[a]	g_{fs}	V_{DS} = −15 V, I_D = −50 A	20			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = −25 V, f = 1 MHz		11400		pF
Output Capacitance	C_{oss}			1200		
Reversen Transfer Capacitance	C_{rss}			900		
Total Gate Charge[c]	Q_g	V_{DS} = −30 V, V_{GS} = −10 V, I_D = −110 A		230	345	nC
Gate-Source Charge[c]	Q_{gs}			50		
Gate-Drain Charge[c]	Q_{gd}			60		
Gate Resistance	R_g	f = 1.0 MHz		3		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = −30 V, R_L = 0.27 Ω I_D ≃ −110 A, V_{GEN} = −10 V, R_g = 2.5 Ω		20	30	ns
Rise Time[c]	t_r			160	240	
Turn-Off Delay Time[c]	$t_{d(off)}$			200	300	
Fall Time[c]	t_f			240	360	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)[b]						
Continuous Current	I_s				−110	A
Pulsed Current	I_{SM}				−240	
Forward Voltage[a]	V_{SD}	I_F = −85 A, V_{GS} = 0 V		−1.0	−1.5	V
Reverse Recovery Time	t_{rr}	I_F = −85 A, di/dt = 100 A/μs		65	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			−4.2	−6.3	A
Reverse Recovery Charge	Q_{rr}			0.14	0.32	μC

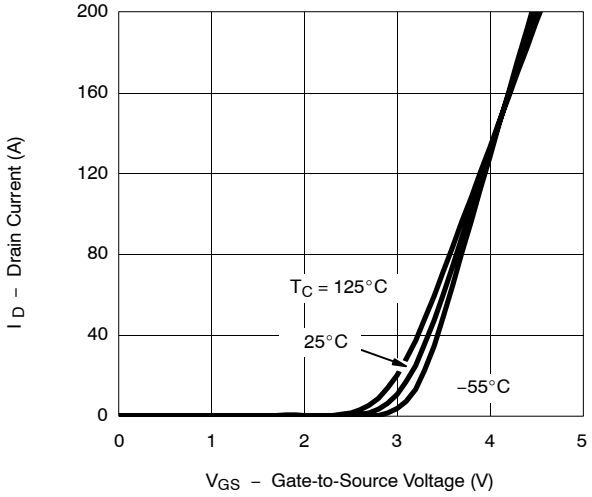
Notes:
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

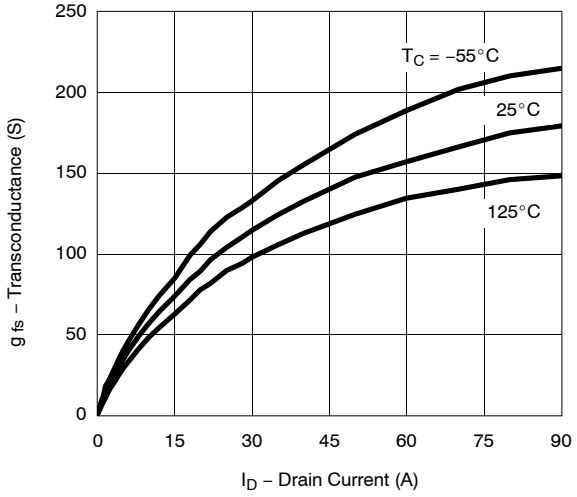
Output Characteristics



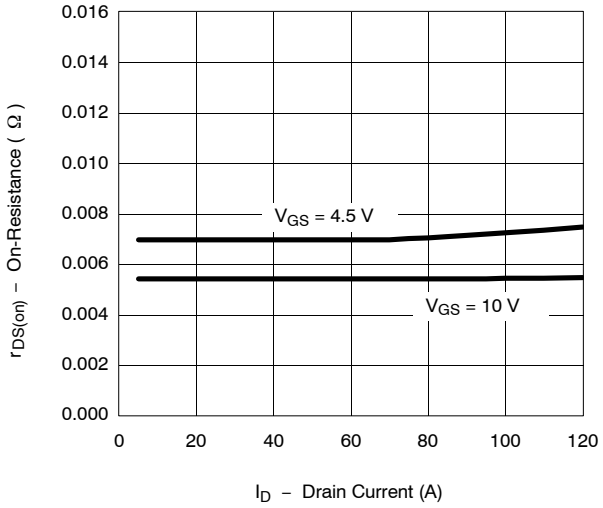
Transfer Characteristics



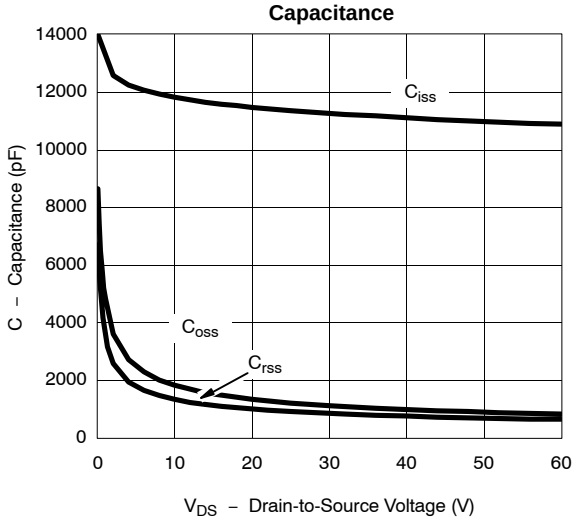
Transconductance



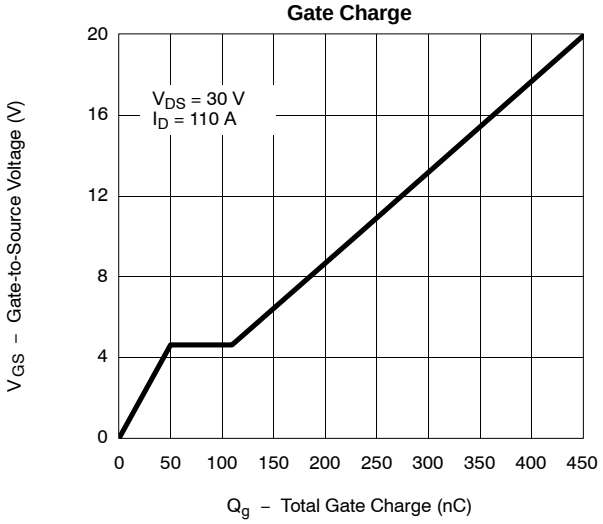
On-Resistance vs. Drain Current



Capacitance

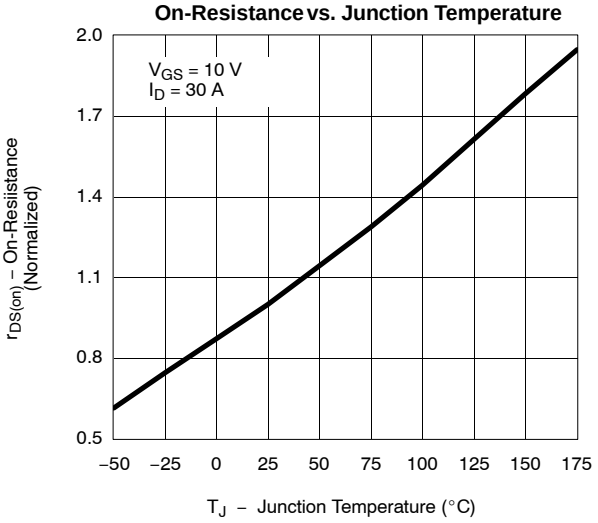


Gate Charge

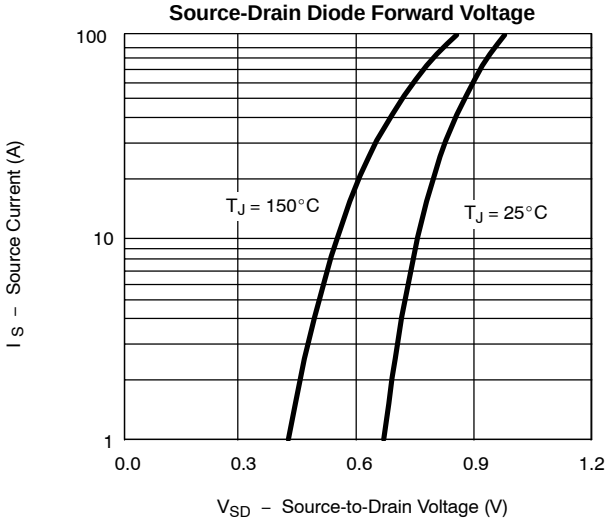


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

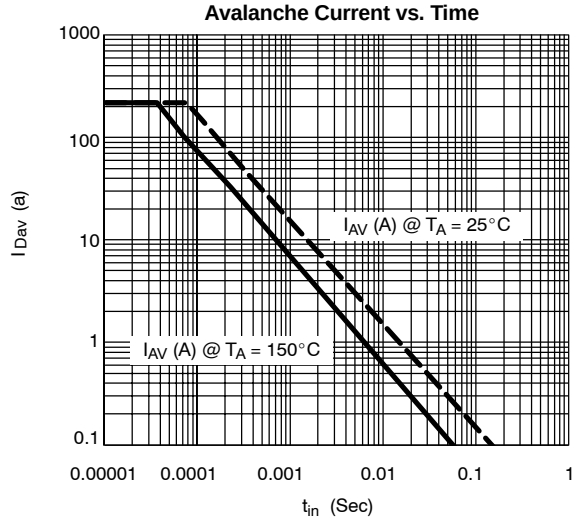
On-Resistance vs. Junction Temperature



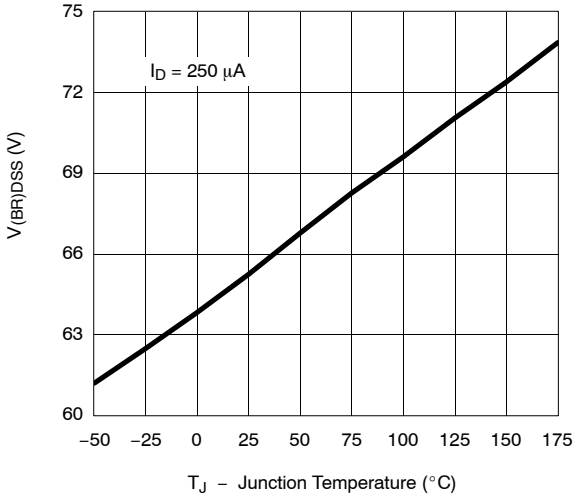
Source-Drain Diode Forward Voltage



Avalanche Current vs. Time

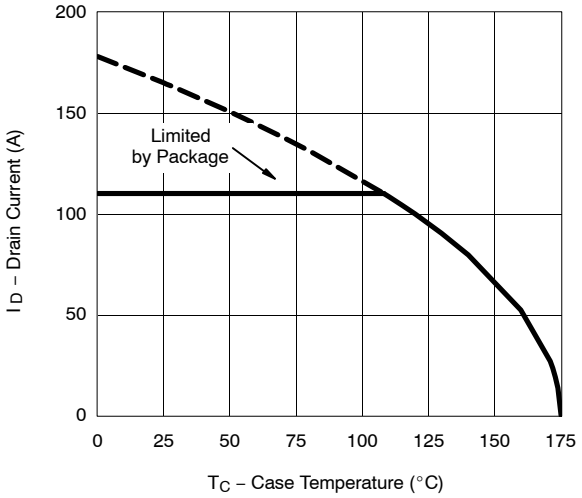


Drain Source Breakdown vs. Junction Temperature

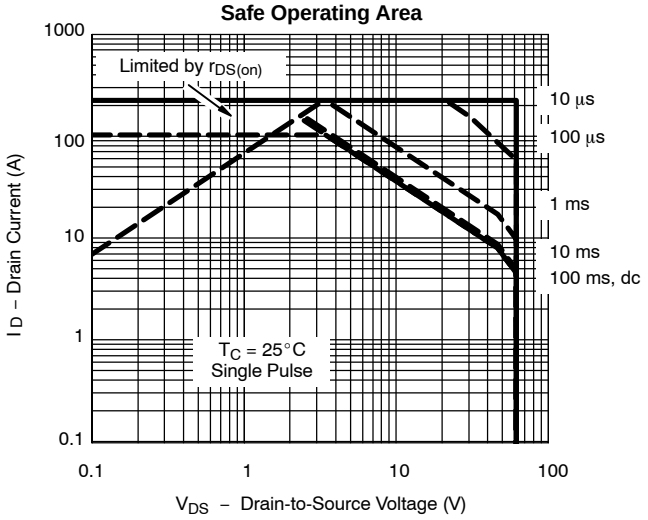


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case